Silicon PNP Power Transistors 2SB860

DESCRIPTION

·With TO-220C package
·Complement to type 2SD1137

APPLICATIONS

·Low frequency power amplifier TV
vertical deflection output applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

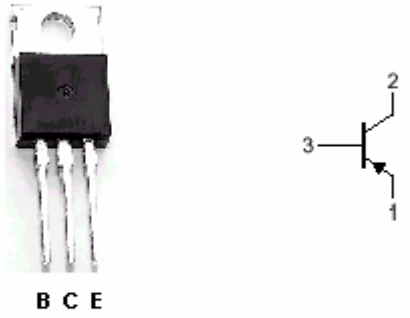

Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-4	V
I_C	Collector current		-4	A
I_{CP}	Collector current-Peak		-5	A
P_C	Collector power dissipation	T_a=25□	1.8	W
		T_C=25□	40	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-45~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-50mA; R_{BE}=∞	-100			V
$V_{(BR)EBO}$	Emitter-base breakdown votage	I_E=-1mA; I_C=0	-4			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-1 A;I_B=-0.1 A			-1.0	V
I_{CEO}	Collector cut-off current	V_{CE}=-80V; R_{BE}=∞			-100	⌠A
I_{EBO}	Collector cut-off current	V_{EB}=-3.5V; I_C=0			-50	⌠A
h_{FE-1}	DC current gain	I_C=-0.5A ; V_{CE}=-4V	50		250	
h_{FE-2}	DC current gain	I_C=-50mA ; V_{CE}=-4V	25		350	

PACKAGE OUTLINE

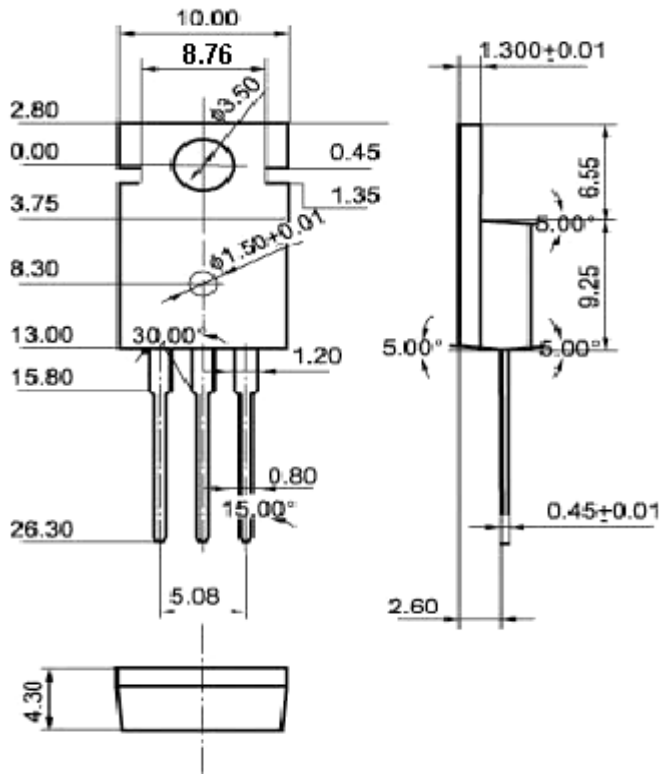

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)

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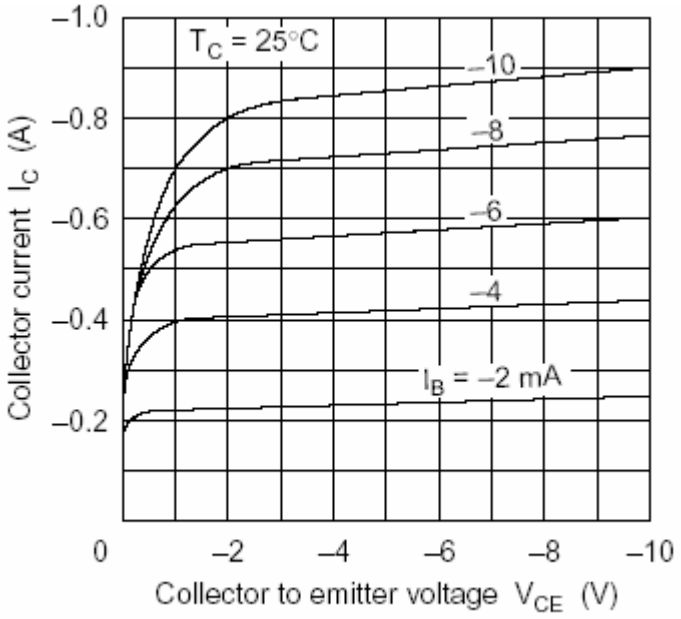

Fig.3 Static Characteristic

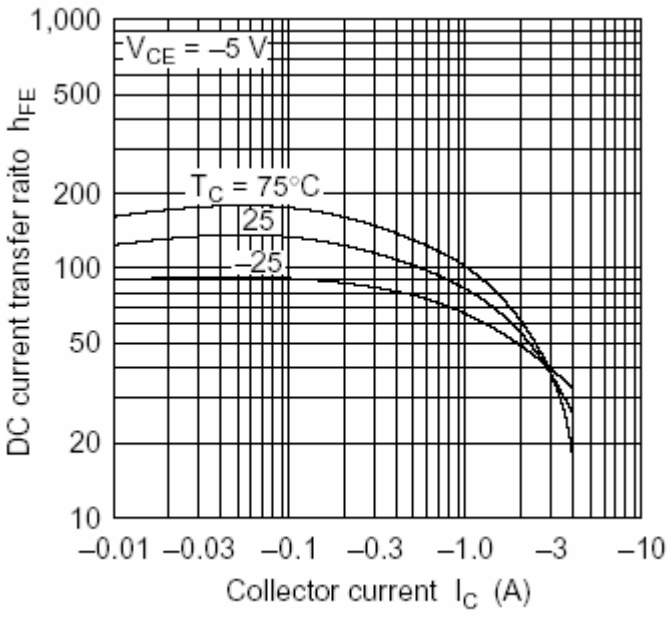

Fig.4 DC current Gain

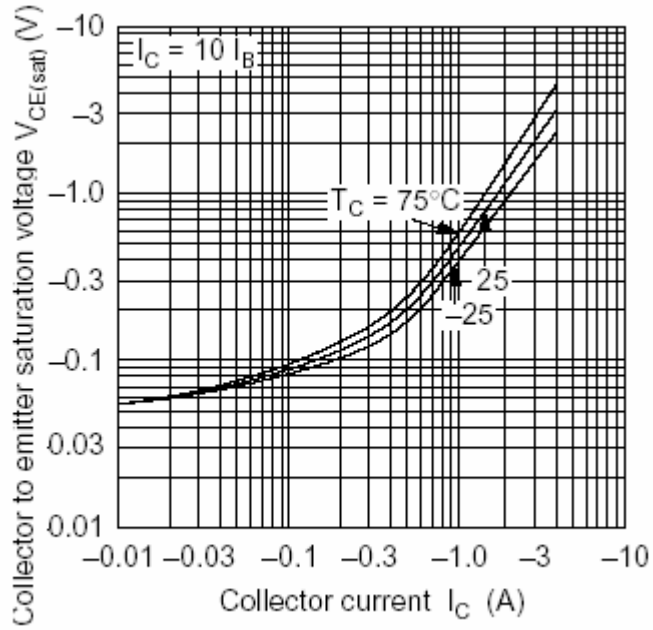

Fig.5 Collector-Emitter Saturation Voltage

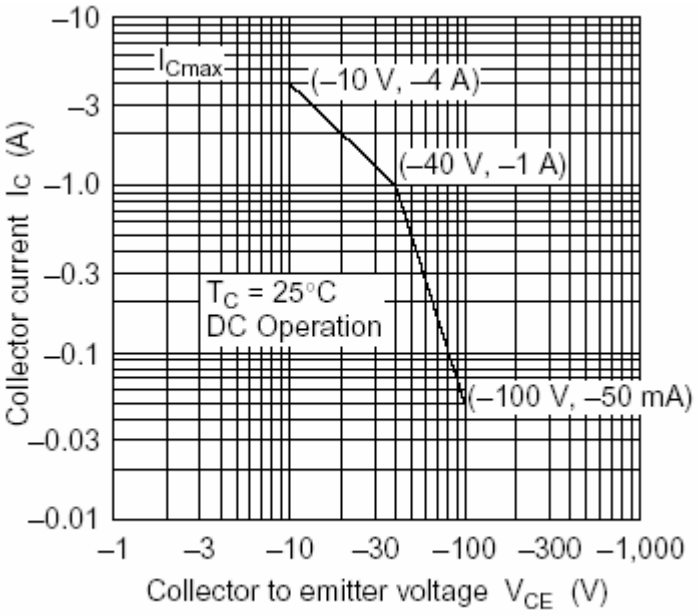

Fig.6 Safe Operating Area